

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

Claim 1 (currently amended): A method for texturing surfaces of silicon wafers comprising the steps of dipping said silicon wafers [(1)] in an etching solution of water, concentrated hydrofluoric acid and concentrated nitric acid and setting a temperature for the etching solution, ~~characterized in that~~ wherein said etching solution [(4)] comprises, in percent, 20% to 55% water, 10% to 40% concentrated hydrofluoric acid and 20% to 60% concentrated nitric acid and ~~in that~~ the temperature of said etching solution [(4)] is between 0 and 15 degrees Celsius.

Claim 2 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said etching solution [(4)] comprises, in percent, 30% to 40% water, 15% to 30% concentrated hydrofluoric acid and 30% to 50% concentrated nitric acid.

Claim 3 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein the temperature of said etching solution [(4)] is between 7 and 9 degrees Celsius.

Claim 4 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said silicon wafers [(1)] remain in said etching solution [(4)] for between 3 and 5 minutes.

Claim 5 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said etching solution [(4)] comprises, in percent, 31% water, 23% concentrated hydrofluoric acid and 46% concentrated nitric acid, in that the temperature of said etching solution [(4)] is 8 degrees Celsius, and ~~in that~~ said silicon wafers [(1)] remain in said etching solution [(4)] for between 1.5 and 2 minutes.

Claim 6 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said silicon wafers [(1)] are oriented substantially vertically and ~~in that~~ said etching solution [(4)] has a flow component.

Claim 7 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said silicon wafers [(1)] are oriented substantially horizontally and ~~in that~~ said etching solution [(4)] is quiescent.

Claim 8 (currently amended): The method as in claim 7, ~~characterized in that~~ wherein said silicon wafers [(1)] are moved through said etching solution [(4)].

Claim 9 (currently amended): The method as in claim 1, ~~characterized in that~~ wherein said silicon wafers [(1)] are polycrystalline.